

[ThA4] Physical Properties of Wide Bandgap Materials

Date / Time May 26 (Thu.), 2022 / 15:15–16:45
Place Convention Hall A
Session Chair Dong-Soo Shin (Hayang University, Korea)

[ThA4-1] Invited

15:15–15:45

Withdrawn

[ThA4-2] Oral

Online 15:45–16:05

Band Alignment and Electronic Properties of Orthorhombic Ga₂O₃ with GaN and AlN Semiconductors

Shibin Krishna, Yi Lu, Che-Hao Liao, Vishal Khandelwal, Xiaohang Li
King Abdullah University of Science and Technology, Saudi Arabia

[ThA4-3] Oral

Online 16:05–16:25

Analyses of Band Alignment in Rocksalt-Structured MgZnO/MgO Interface

Masaki Matsuda¹, Kotaro Ogawa^{1,2}, Yuichi Ota³, Tomohiro Yamaguchi¹, Kentaro Kaneko⁴, Shizuo Fujita⁴,
Tohru Honda¹, Takeyoshi Onuma¹

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Technology Research Institute, Japan, ⁴Kyoto University, Japan

[ThA4-4] Oral

Offline 16:25–16:45

Dislocation Analysis of GaN-Based Light Emitting Diodes Using High Resolution Raman Spectroscopy

YoungMin Park¹, HyunDon Jung¹, Dong-Soo Shin², Jong-In Shim²

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